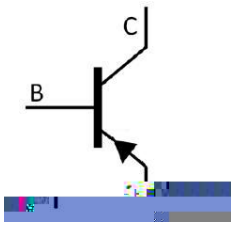
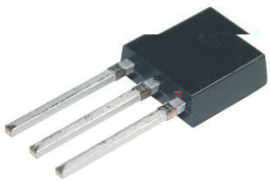
TO-251 PNP Silicon PNP transistor in a TO-251 Plastic Package.

, 2SD880I

Low collector saturation voltage, collector power dissipation, complementary to 2SD880I.

Audio frequency power amplifier applications.



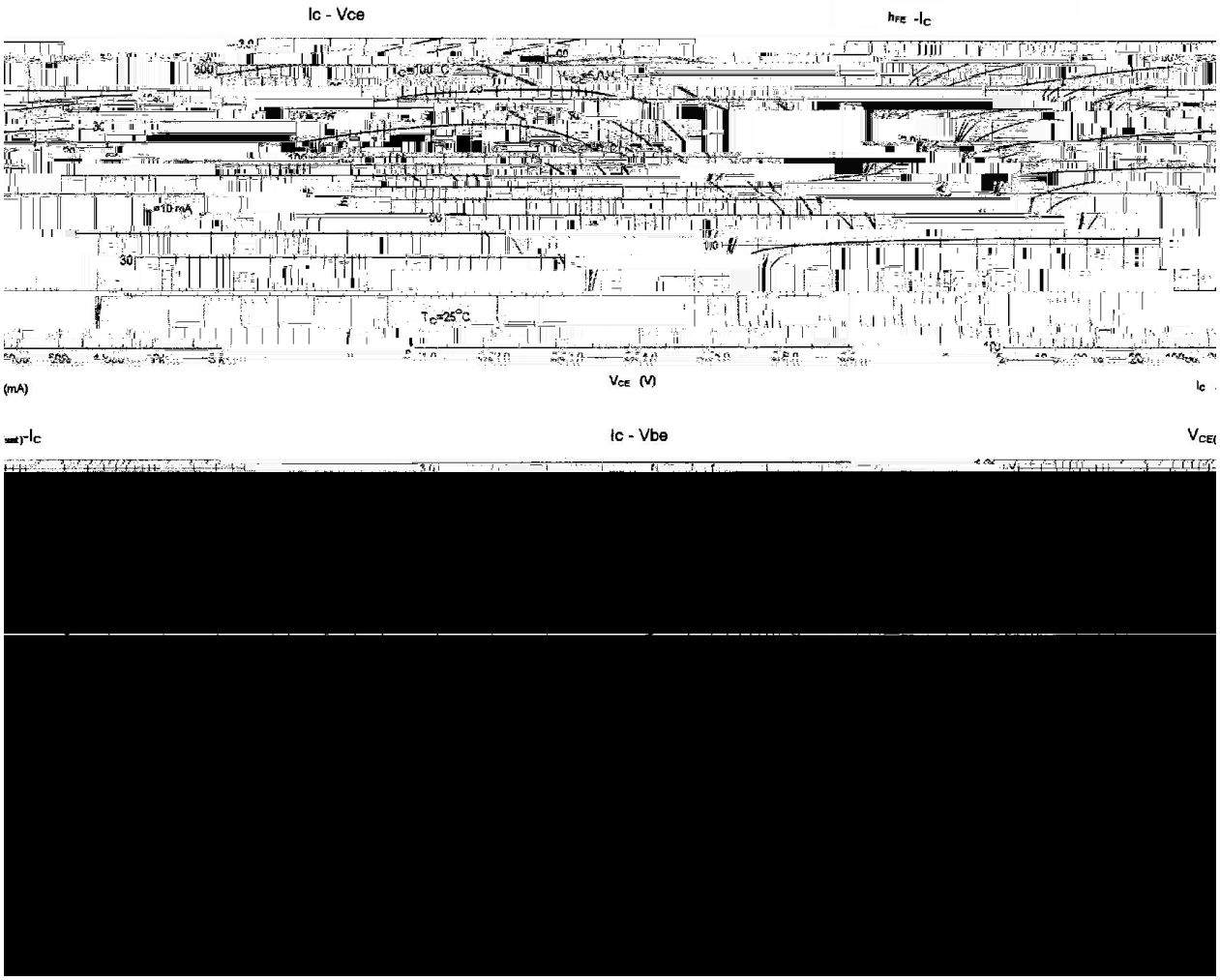


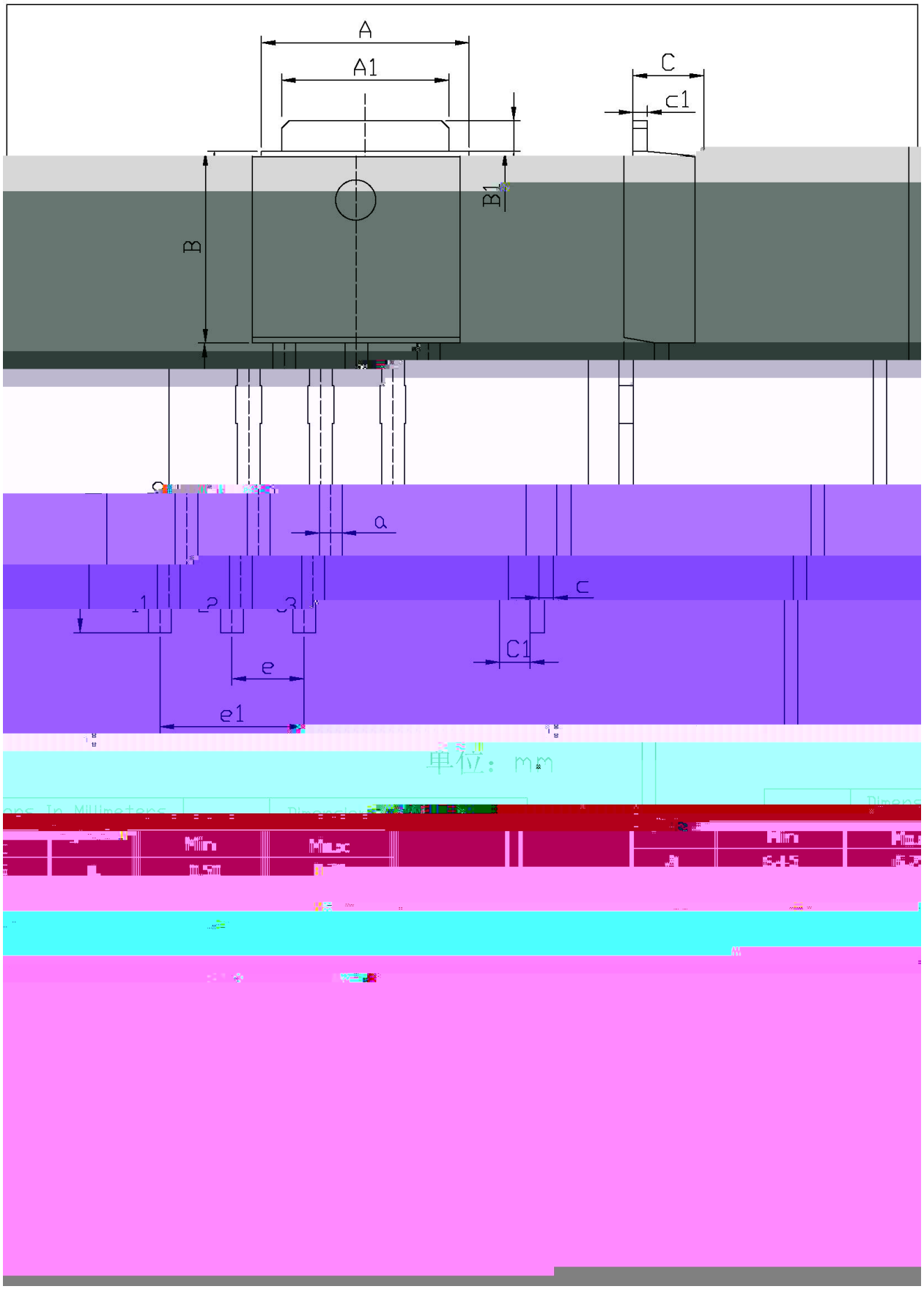
PIN1 Base PIN 2 Collector PIN 3 Emitter

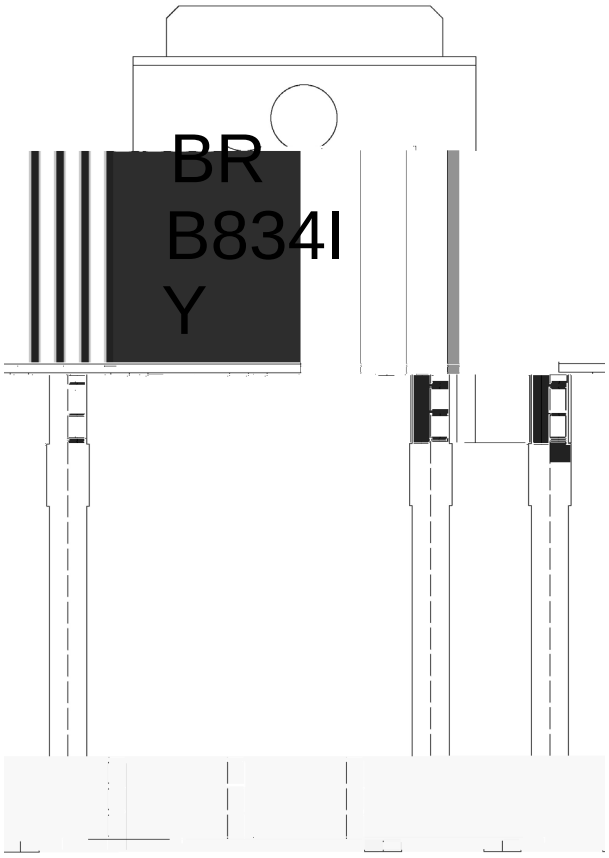
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current - Continuous	I_B	-0.5	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-50mA I_B=0	-60			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-60V I_E=0			-100	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-7.0V I_C=0			-100	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=-5.0V I_C=-0.5A	60		300	
	$h_{FE(2)}$	V_{CE}=-5.0V I_C=-3.0A	20			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-3.0A I_B=-0.3A		-0.5	-1.0	V

Base to Emitter Voat)


Ic - Vce
hFE -Ic
(mA)
VCE (V)
Ic
Ic - Vbe


A
A1
C
c1
B
B1
a
c
C1
e
e1
单位：mm



BR

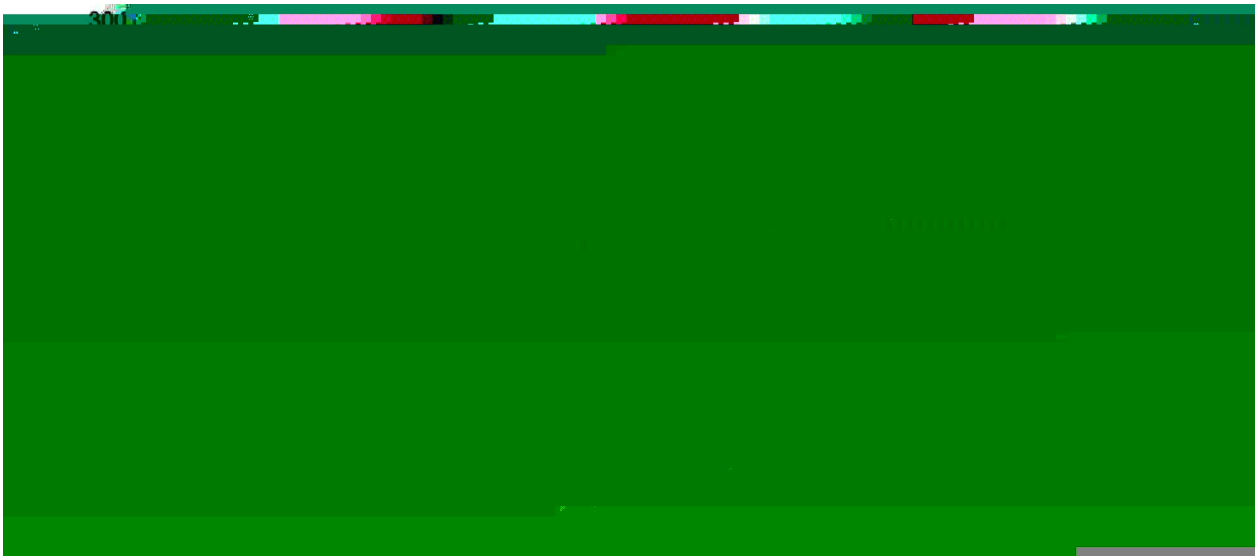
B834I

Y: h_{FE}

****

Note:

BR:	Company Code
B834I:	Product Type.
Y:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.



		Note:	
1	25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2	255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱